

IN THE CLAIMS

Presented below are all of the pending claims, with status identifiers as promulgated in the Interim Revised Format directions.

1 1. (Cancelled).

2 2. (Currently amended) ~~The apparatus of claim 1~~ An
3 apparatus, comprising:

4 a metal-oxide-semiconductor transistor;

5 a metallic gate electrode coupled to a diffused gate region of said

6 metal-oxide-semiconductor transistor and to a positive voltage source;

7 and

8 a metallic source electrode and a metallic drain electrode coupled

9 to said metal-oxide-semiconductor transistor and to each other and to a

10 negative voltage source, wherein said metal-oxide-semiconductor

11 transistor includes a the diffused gate region formed from material with

a work function less than - 0.56 volts.

1 3. (Currently amended) The apparatus of claim 2, wherein

2 said ~~diffused gate region~~ material of said diffused gate region is

3 platinum silicate.

1 4. (Currently amended) The apparatus of claim 2, wherein

2 said ~~diffused gate region~~ material of said diffused gate region is selected

3 from the group consisting of tantalum nitrate, iridium, nickel, and
4 arsenic.

1 5. (Currently amended) The apparatus of claim 1 2, wherein
2 said metal-oxide-semiconductor transistor includes a heavily-doped
3 substrate area.

1 6. (Currently amended) The apparatus of claim 1 2, wherein
2 said metal-oxide-semiconductor transistor is a p-channel device.

1 7. (Currently amended) The apparatus of claim 1 2, wherein
2 said metal-oxide-transistor is an n-channel device.

1 15. through 19. (Cancelled)

1 20. (Currently amended) An apparatus, comprising:
2 a metallic gate electrode to couple to a positive power supply
3 voltage;
4 a diffused gate region ~~with a~~ formed from a material whose
5 work function is less than minus 0.56 volts;
6 a gate insulator area;
7 a channel area coupled to said gate insulator area;
8 a diffused drain area coupled to said channel area; and
9 a diffused source area coupled to said channel area.

1 21. (Previously added) The apparatus of claim 20, wherein said
2 material is platinum silicate.

1 22. (Previously added) The apparatus of claim 20, wherein said
2 material is selected from the group consisting of tantalum nitrate,
3 iridium, nickel, and arsenic.

1 23. (Previously added) The apparatus of claim 20, further
2 comprising a substrate which is heavily-doped.